

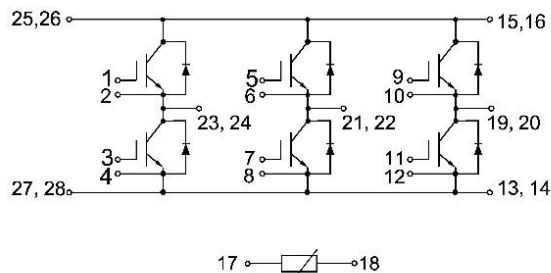
GT75FF120T5H

Circuit Diagram

IGBT Module

Features:

- $V_{CES}=1200V$ $I_C=75A$ Trench & Field Stop IGBT Module
- Short Circuit Capability
- Low Switching Loss
- 100% RBSOA Tested($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Auxiliary Inverters
- Motor Drives
- Servo Drives

Type	Package	Marking
GT75FF120T5H	T5	GT75FF120T5H

IGBT, Inverter

Maximum Rated Values ($T_C=25^\circ C$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current Limited by T_{Jmax}	$T_C=100^\circ C$	75	A
		$T_C=25^\circ C$	150	A
I_{CM}	Peak Collector Current Repetitive	T_p limited by T_{Jmax}	150	A
P_D	Maximum Power Dissipation (IGBT)	$T_C=25^\circ C, T_{Jmax}=175^\circ C$	520	W

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Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.4\text{mA}$, $V_{CE}=V_{GE}$	4.9	5.7	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=75\text{A}$, $V_{GE}=15\text{V}$	$T_J=25^{\circ}\text{C}$	1.70	2.05	V
			$T_J=125^{\circ}\text{C}$	2.13		V
			$T_J=175^{\circ}\text{C}$	2.28		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}$, $V_{CE}=1200\text{V}$, $T_J=25^{\circ}\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=20\text{V}$, $V_{CE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			200	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=100\text{kHz}$		7705		pF
C_{oes}	Output Capacitance			415		pF
C_{res}	Reverse Transfer Capacitance			80		pF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V, I_C=75A,$ $R_{Gon}=15\Omega, V_{GE}=\pm 15V,$ Inductive Load	$T_J=25^{\circ}C$		174		ns
			$T_J=125^{\circ}C$		176		
			$T_J=175^{\circ}C$		178		
t_r	Rise Time		$T_J=25^{\circ}C$		65		ns
			$T_J=125^{\circ}C$		79		
			$T_J=175^{\circ}C$		85		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^{\circ}C$		282		ns
			$T_J=125^{\circ}C$		318		
			$T_J=175^{\circ}C$		336		
t_f	Fall Time	$T_J=25^{\circ}C$		175		ns	
		$T_J=125^{\circ}C$		244			
		$T_J=175^{\circ}C$		310			
E_{on}	Turn-on Switching Loss	$V_{CC}=600V, I_C=75A,$ $R_{Gon}=15\Omega, V_{GE}=\pm 15V,$ $di/dt=700A/\mu s(T_J=175^{\circ}C)$ Inductive Load	$T_J=25^{\circ}C$		8.4		mJ
		$T_J=125^{\circ}C$		11.4			
		$T_J=175^{\circ}C$		13.2			

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E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =75A, R _{Goff} =15Ω, V _{GE} =±15V, du/dt=5200V/μs(T _J =175°C) Inductive Load	T _J =25°C		5.2		mJ
			T _J =125°C		7.0		
			T _J =175°C		8.0		
Q _g	Total Gate Charge	V _{GE} =+15V...-15V	T _J =25°C		440		nC
R _{G (int)}	Internal Gate Resistance		T _J =25°C		7.6		Ω
T _{SC}	V _{CC} =600V, V _{GE} =±15V, T _J =175°C ^{note1}					10	us
R _{θJC}	IGBT Thermal Resistance: Junction-to-Case (per IGBT)					0.287	°C/W
R _{θCS}	IGBT Thermal Resistance: Case-to-Sink (per IGBT) (per IGBT, λ _{grease} = 1 W/(m · K))				0.198		°C/W

note1: Short circuit withstand time cannot exceed 10us under specified condition

Diode, Inverter

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1200	V
I _F	Diode Continuous Forward Current		75	A
I _{FM}	Diode Maximum Forward Current	tp=1ms	150	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _{FM}	Forward Voltage	I _F =75A	T _J =25°C		1.65	2.00	V
			T _J =125°C		1.75		
			T _J =175°C		1.83		
t _{rr}	Reverse Recovery Time	I _F =75A, -diF/dt=830A/μs(T _J =175°C), V _R =600V, V _{GE} =-15V	T _J =25°C		304		ns
			T _J =125°C		455		
			T _J =175°C		572		
I _{rr}	Peak Reverse Recovery Current		T _J =25°C		35		A
			T _J =125°C		40		
			T _J =175°C		43		
Q _{rr}	Reverse Recovery Charge		T _J =25°C		5.1		μC
			T _J =125°C		5.9		
			T _J =175°C		12.3		



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E _{rec}	Reverse Recovery Energy	I _F =75A, -diF/dt=830A/μs(T _J =175°C), V _R =600V, V _{GE} =-15V	T _J =25°C		1.5		mJ
			T _J =125°C		3.1		
			T _J =175°C		4.4		
R _{θJC}	Diode Thermal Resistance: Junction-to-Case (per Diode)					0.499	°C/W
R _{θCS}	Diode Thermal Resistance: Case-to-Sink (per Diode, λ _{grease} = 1 W/(m • K))				0.345		°C/W

Internal NTC-Thermistor Characteristics

Symbol	Conditions	Min.	Typ.	Max.	Units.
R ₂₅	T _C =25°C		5		kΩ
ΔR/R	T _C =100°C, R ₁₀₀ =465Ω	-5		+5	%
P ₂₅	T _C =25°C			10	mW
B _{25/50}	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]		3380		K
B _{25/80}	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]		3440		K
B _{25/100}	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]		3545		K

Module

Symbol	Description	Min.	Typ.	Max.	Units
V _{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f=50Hz, 60s		2500	V
T _J	Maximum Junction Temperature	-40		175	°C
T _{JOP}	Maximum Operating Junction Temperature Range ^{note2}	-40		150	°C
T _{stg}	Storage Temperature	-40		125	°C
CTI	Comparative Tracking Index	200			
T	Power Terminals Screw:M5	3		6	N·m
G	Weight		190		g

note2: T_{JOP}> 150°C is only allowed for operation at overload conditions.

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IGBT Module Datasheet



Ordering Information Table

Device code	G	T	75	FF	120	T5	H
	①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Field Stop Trench Gate IGBT
- ③ - Rated Current (75=75A)
- ④ - Circuit Configuration:FF (Full Bridge)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)



Characteristic diagram

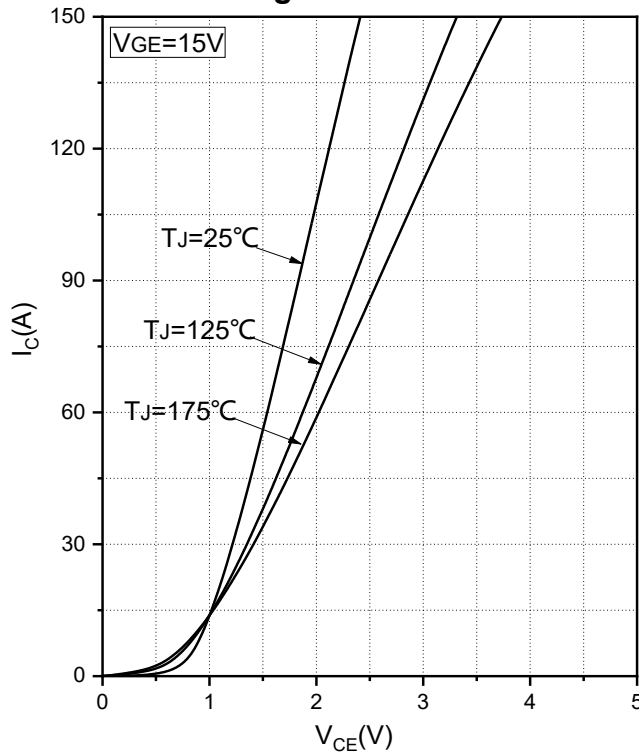


Fig.1 Typical Saturation Voltage Characteristics

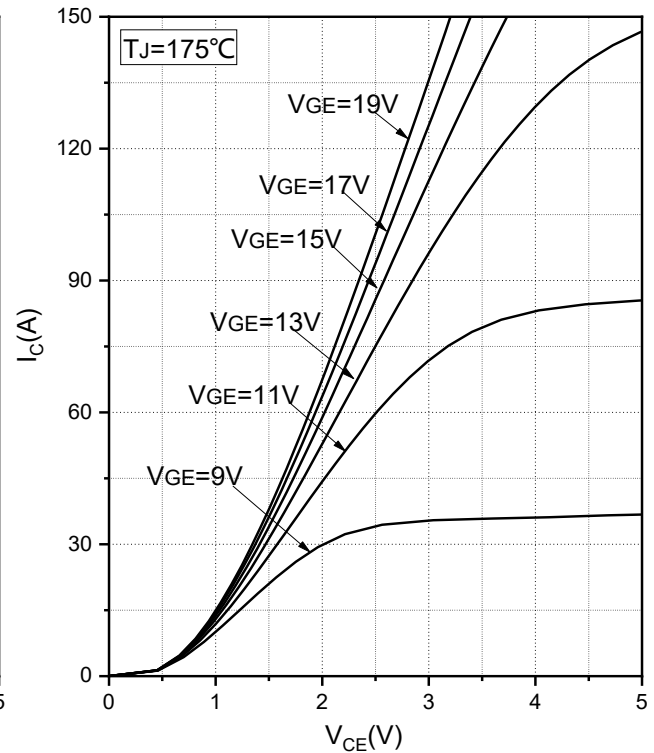


Fig.2 Typical Output Characteristics

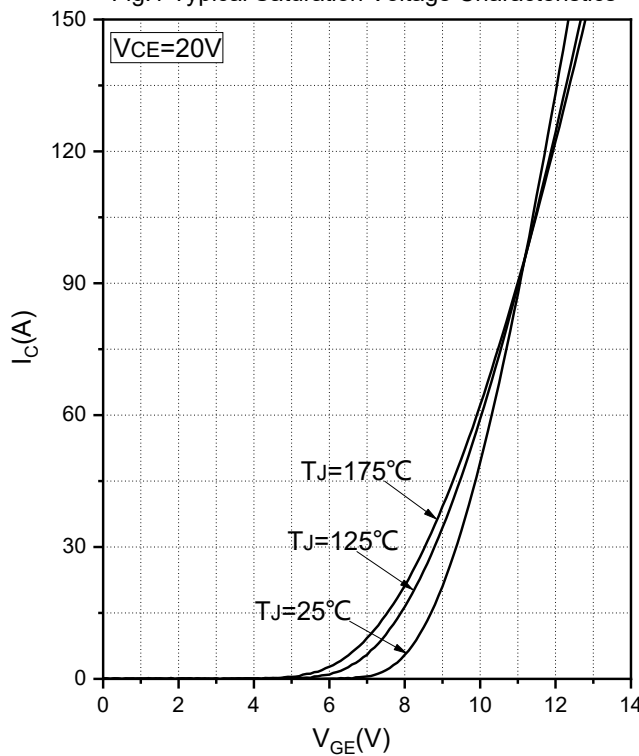


Fig.3 Transfer Characteristic

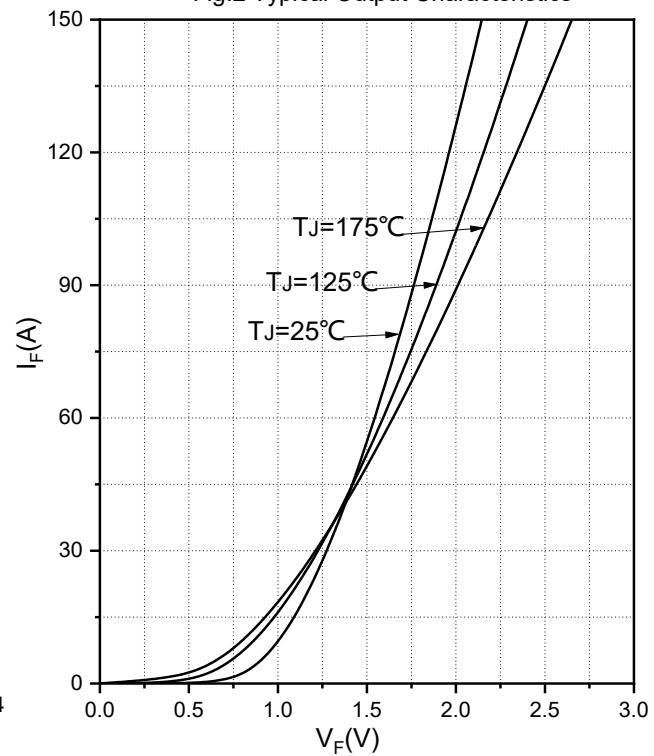


Fig.4 Forward Characteristics of Diode

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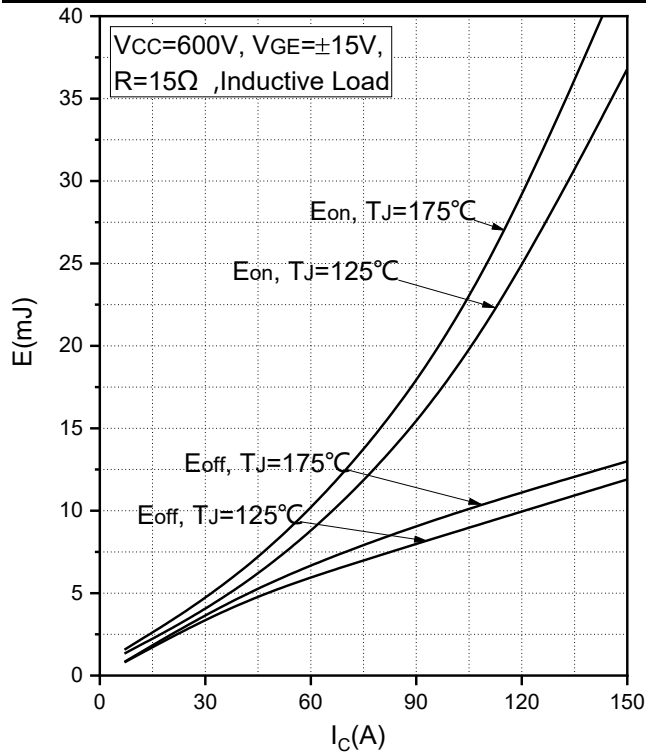


Fig.5 Typical Switching Loss vs. Collector Current

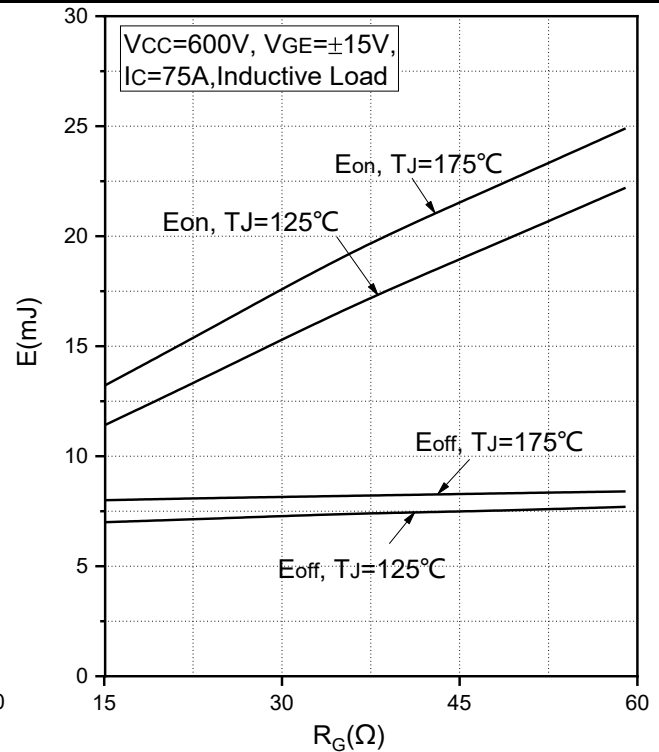


Fig.6 Typical Switching Loss vs. Gate Resistance

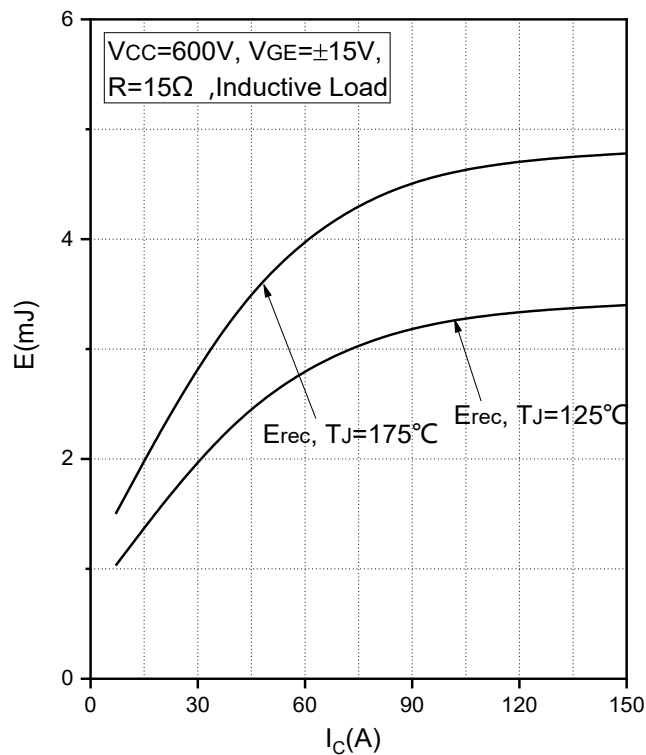


Fig.7 Typical Switching Loss vs. Forward Current

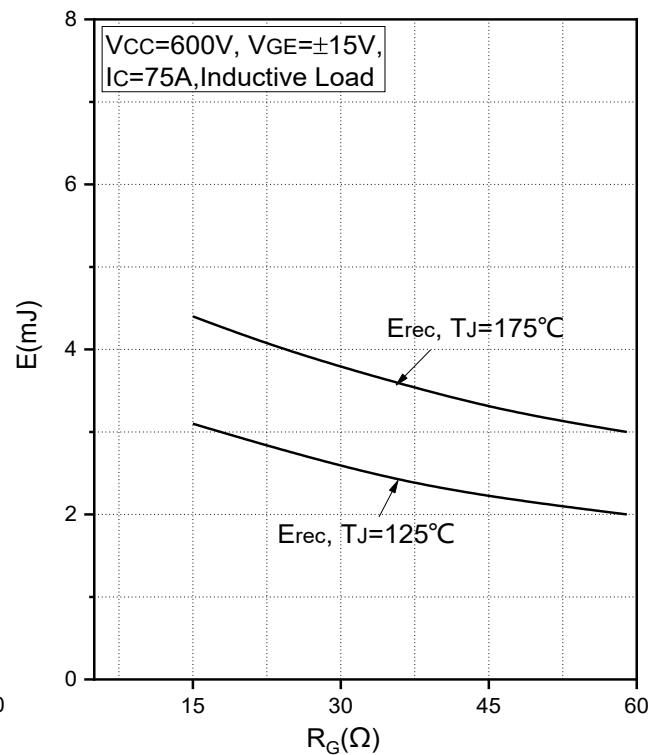


Fig.8 Typical Switching Loss vs. Gate Resistance

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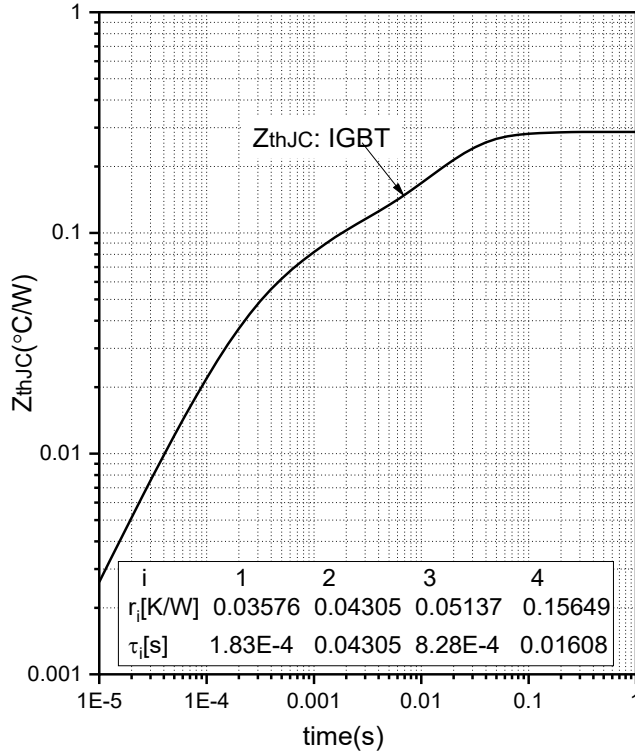


Fig.9 Transient Thermal Impedance (IGBT)

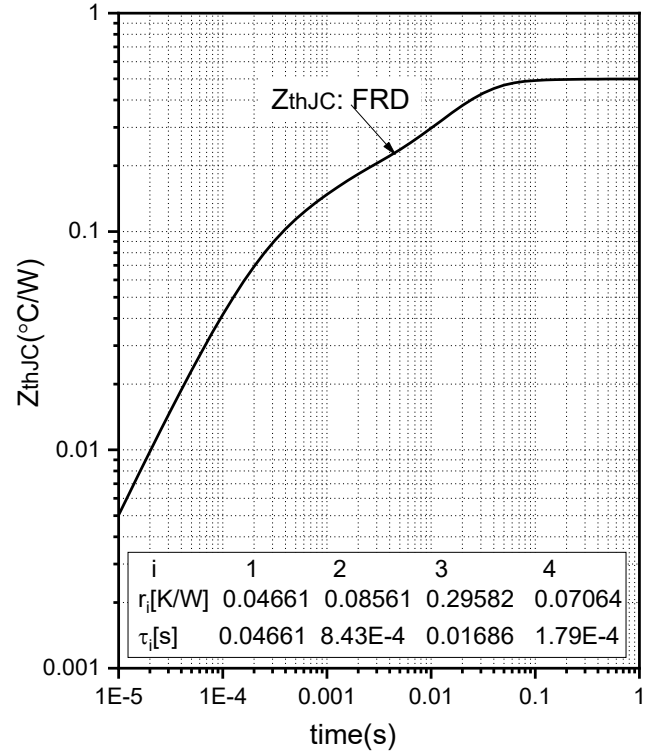


Fig.10 Transient Thermal Impedance (Diode)

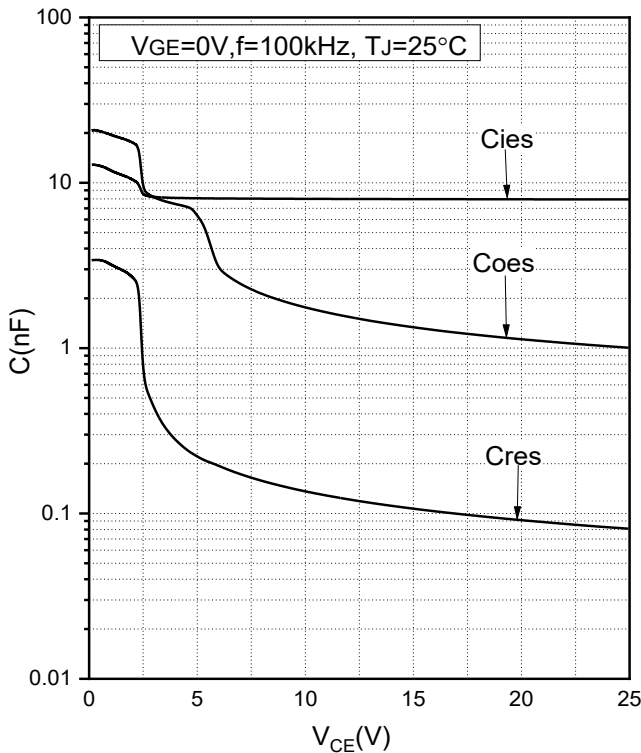


Fig.11 Capacitance Characteristics

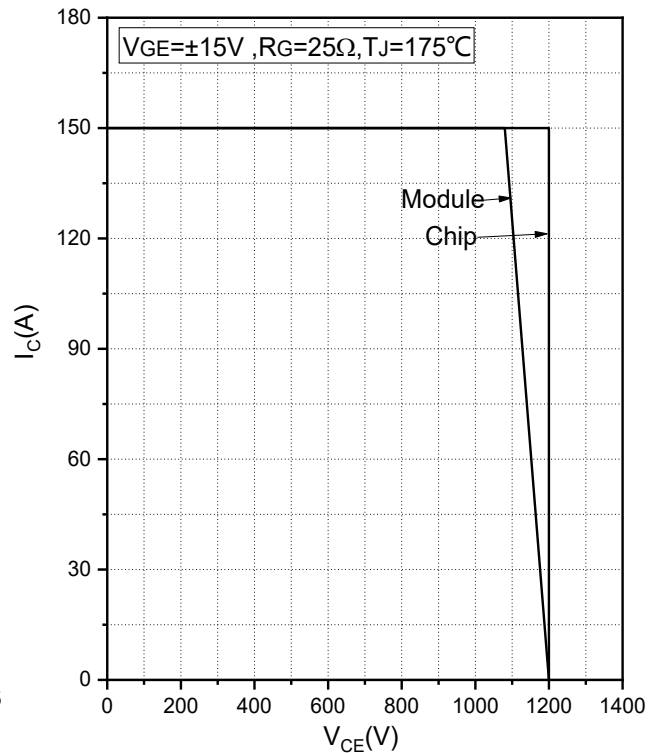


Fig.12 Reverse Bias Safe Operation Area (RBSOA)

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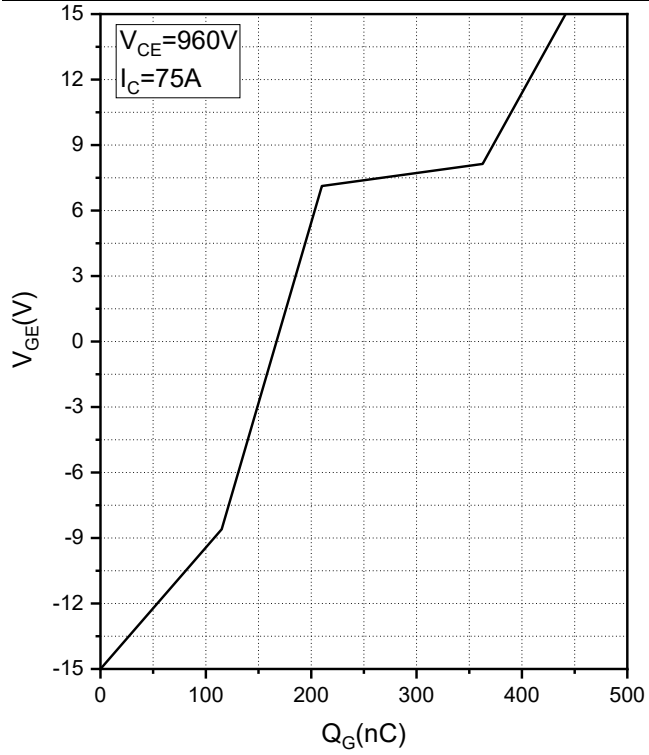


Fig.13 Gate Charge Characteristics

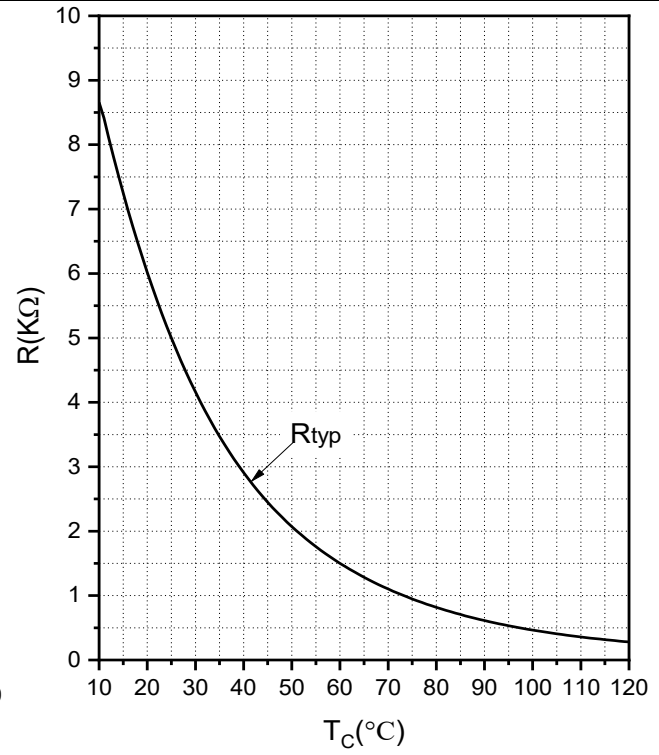


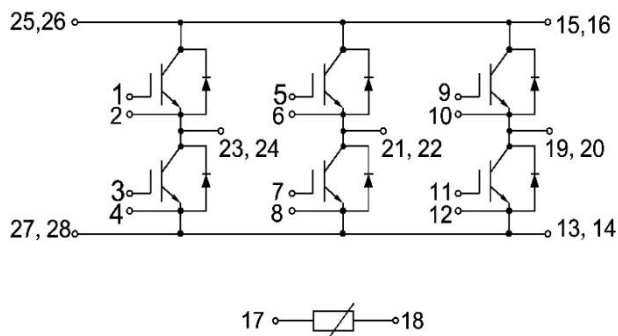
Fig.14 NTC Temperature Characteristics



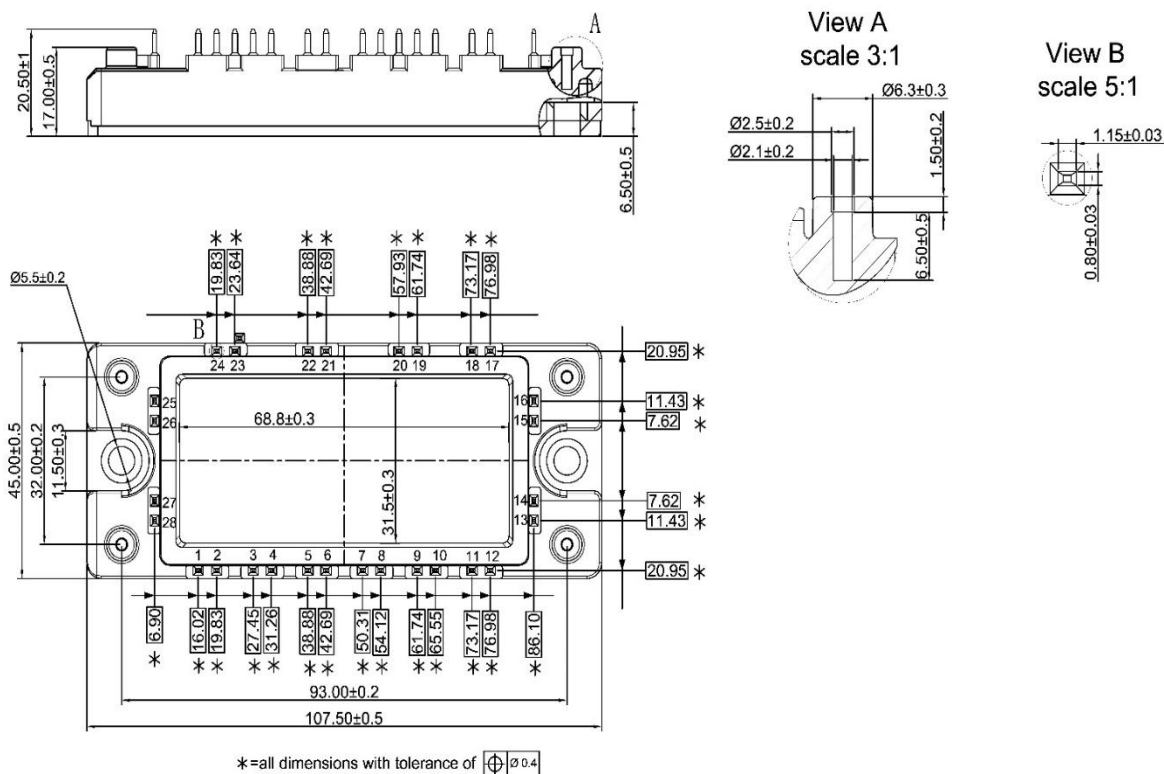
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Internal Circuit:



Package Outline (Unit: mm):





Revision	Notes
A	Fina Datasheet Initial Release

Announcement

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